

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-22 (canceled).

Claim 23 (currently amended): A method for fabricating a semiconductor device, the method including:

forming an amorphous silicon film on a substrate;

preprocessing the amorphous silicon film by modifying the amorphous silicon film to prepare the amorphous silicon film to be made polycrystalline;

laser processing the amorphous silicon film modified through the preprocessing step for producing a polycrystalline silicon film; and

laser power inspecting/extracting for inspecting for the presence of a foreign object or an abnormality in the preprocessing step by use of the amorphous silicon film having undergone the preprocessing step, and for determining a laser power based on a predetermined inspection performed on a predetermined region of the amorphous silicon film having undergone the preprocessing step; wherein

the laser processing step uses the laser power determined in the laser power inspection/extraction step.

Claim 24 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes determining the laser power through inspection using spectroscopy.

Claim 25 (previously presented): The method of claim 24, wherein the spectroscopy is performed at a measurement wavelength of about 700 nm to about 800 nm.

Claim 26 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes determining the laser power through inspection using imaging whereby light shines on a measurement spot to detect an image acquired by targeting the measurement spot.

Claim 27 (canceled).

Claim 28 (previously presented): The method of claim 24, wherein the inspection using the spectroscopy is performed with measurement light shining on a measurement spot from around the measurement spot.

Claim 29 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes performing an inspection adjacent laser processing equipment that performs the laser processing in the laser processing step.

Claim 30 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting a film surface on the substrate.

Claim 31 (canceled).

Claim 32 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes setting a measurement fixed-quantity value against which to evaluate measurement results.

Claim 33 (previously presented): The method of claim 32, wherein the measurement fixed-quantity value is determined by using equipment having a calibration substrate placed thereon and provided with a function for performing calibration.

Claim 34 (currently amended): The method of claim 23, wherein the laser power inspection/extraction step includes ~~performing an inspection by using equipment provided with both a function for inspecting the polycrystalline silicon film and a function for automatically~~ determining an optimum laser power value and automatically feeding the automatically determined optimum laser power value to laser processing equipment ~~used in the laser processing step.~~

Claim 35 (previously presented): The method of claim 23, wherein the laser processing step includes using a laser power about 5 mJ or about 10 mJ lower than an optimum laser power value determined in the laser power inspection/extraction step.

Claim 36 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes performing multiple-point measurement inspection on the polycrystalline silicon film.

Claim 37 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting, before the laser processing, the film on the substrate to find a ratio of amorphous silicon film to polycrystalline silicon film.

Claim 38 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting, after the laser processing, the film on the substrate to find a ratio of amorphous silicon film to polycrystalline silicon film.

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Claim 39 (previously presented): The method of claim 23, wherein the laser power inspection/extraction step includes inspecting, both before and after the laser processing, the film on the substrate to find a ratio of amorphous silicon film to polycrystalline silicon film.

Claims 40-44 (canceled).